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ABSTRACT

A semiconductor device including a semiconductor substrate having a grid-line area and a chip area, the chip area having a circuit area and a dummy area surrounding the circuit area, circuit patterns formed on the substrate in the circuit area, a first dummy pattern which is formed of the same material as the circuit pattern, formed in the dummy area, the dummy pattern encompassing the circuit area, a first insulating layer formed on an entire surface of the semiconductor substrate, a second insulating layer formed only on the first insulating layer which is formed on the semiconductor substrate and on the circuit patterns; and a third insulating layer formed on the exposed first insulating layer and the second insulating layer.

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